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1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the following device numbers: RN60, RN48 and RN32.

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

S 9 S08 RN AA F1 B CC

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

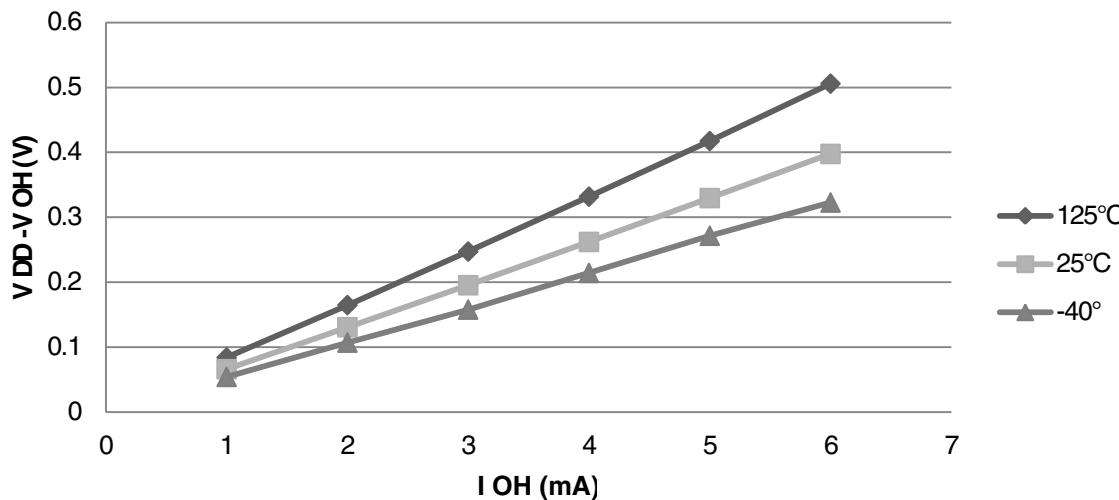
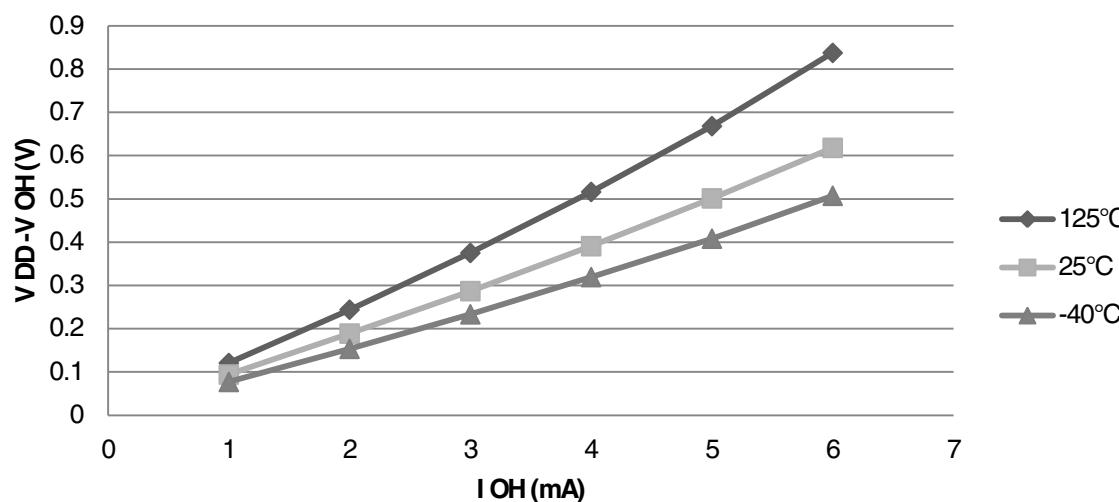
Field	Description	Values
S	Qualification status	<ul style="list-style-type: none"> S = fully qualified, general market flow
9	Memory	<ul style="list-style-type: none"> 9 = flash based
S08	Core	<ul style="list-style-type: none"> S08 = 8-bit CPU
RN	Device family	<ul style="list-style-type: none"> RN
AA	Approximate flash size in KB	<ul style="list-style-type: none"> 60 = 60 KB 48 = 48 KB 32 = 32 KB
F1	Fab and mask set identifier	<ul style="list-style-type: none"> W1
B	Temperature range (°C)	<ul style="list-style-type: none"> M = -40 to 125

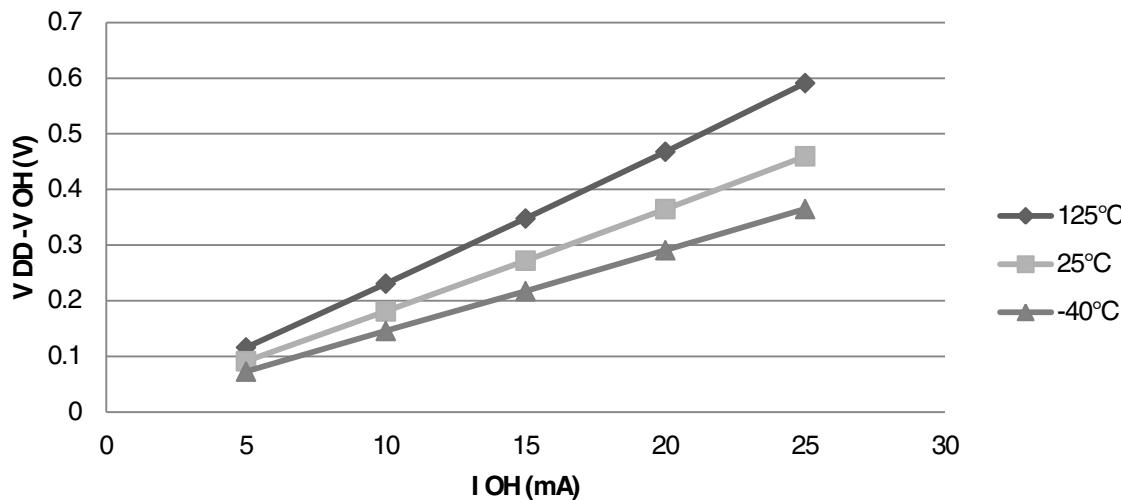
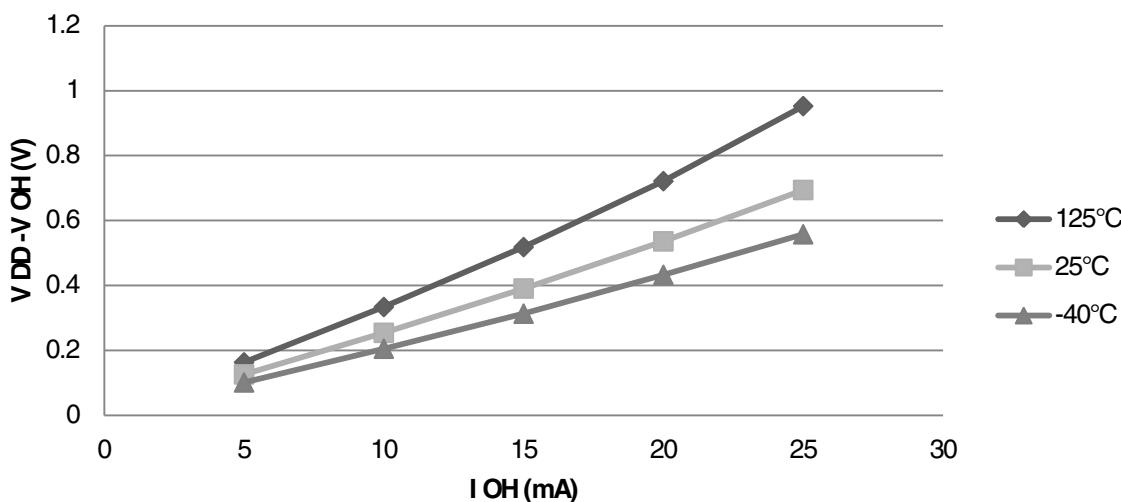
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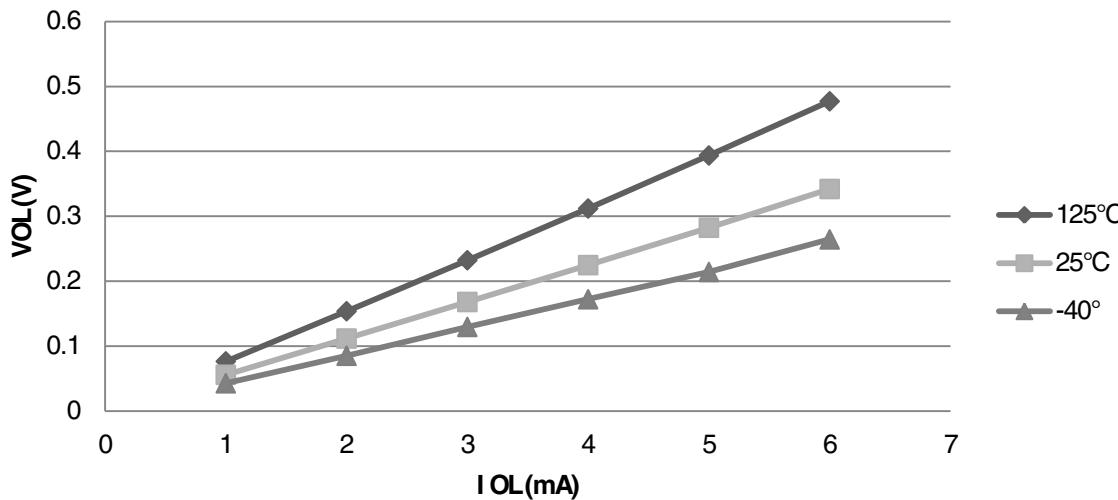
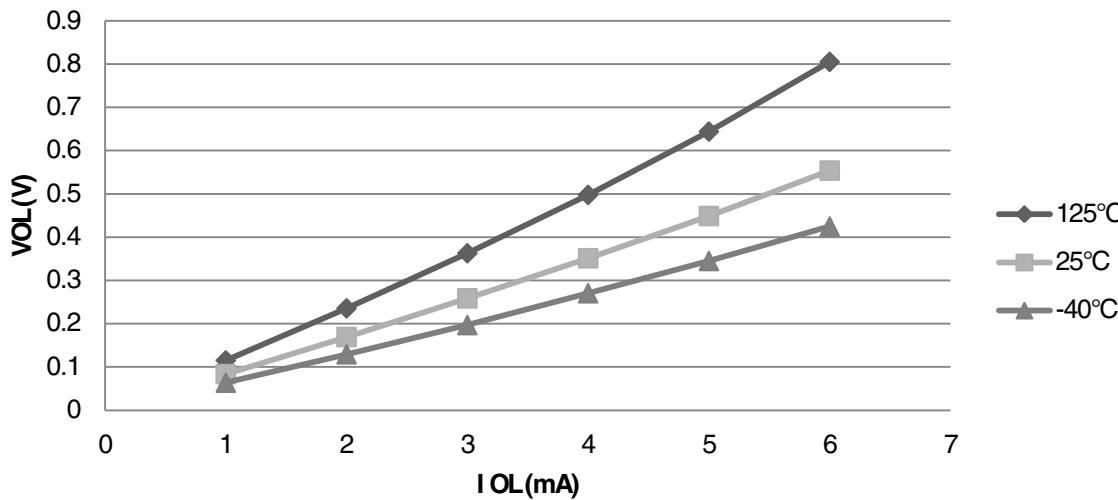
Table 3. LVD and POR Specification (continued)

Symbol	C	Description		Min	Typ	Max	Unit
V_{LVDH}	C	Falling low-voltage detect threshold - high range (LVDV = 1) ³		4.2	4.3	4.4	V
V_{LVW1H}	C	Falling low-voltage warning threshold - high range	Level 1 falling ($LVWV = 00$)	4.3	4.4	4.5	V
V_{LVW2H}	C		Level 2 falling ($LVWV = 01$)	4.5	4.5	4.6	V
V_{LVW3H}	C		Level 3 falling ($LVWV = 10$)	4.6	4.6	4.7	V
V_{LVW4H}	C		Level 4 falling ($LVWV = 11$)	4.7	4.7	4.8	V
V_{HYSH}	C	High range low-voltage detect/warning hysteresis		—	100	—	mV
V_{LVDL}	C	Falling low-voltage detect threshold - low range (LVDV = 0)		2.56	2.61	2.66	V
V_{LVDW1L}	C	Falling low-voltage warning threshold - low range	Level 1 falling ($LVWV = 00$)	2.62	2.7	2.78	V
V_{LVDW2L}	C		Level 2 falling ($LVWV = 01$)	2.72	2.8	2.88	V
V_{LVDW3L}	C		Level 3 falling ($LVWV = 10$)	2.82	2.9	2.98	V
V_{LVDW4L}	C		Level 4 falling ($LVWV = 11$)	2.92	3.0	3.08	V
V_{HYSDL}	C	Low range low-voltage detect hysteresis		—	40	—	mV
V_{HYSWL}	C	Low range low-voltage warning hysteresis		—	80	—	mV
V_{BG}	P	Buffered bandgap output ⁴		1.14	1.16	1.18	V

1. Maximum is highest voltage that POR is guaranteed.
2. POR ramp time must be longer than 20us/V to get a stable startup.
3. Rising thresholds are falling threshold + hysteresis.
4. Voltage factory trimmed at $V_{DD} = 5.0$ V, Temp = 125 °C

Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (low drive strength) ($V_{DD} = 5\text{ V}$)**Figure 1. Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (standard drive strength) ($V_{DD} = 5\text{ V}$)****Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (low drive strength) ($V_{DD} = 3\text{ V}$)****Figure 2. Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (standard drive strength) ($V_{DD} = 3\text{ V}$)**

Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (high drive strength) ($V_{DD} = 5\text{ V}$)**Figure 3. Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (high drive strength) ($V_{DD} = 5\text{ V}$)****Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (high drive strength) ($V_{DD} = 3\text{ V}$)****Figure 4. Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (high drive strength) ($V_{DD} = 3\text{ V}$)**

Typical I_{OL} Vs. V_{OL}(low drive strength) (V_{DD} = 5 V)**Figure 5. Typical I_{OL} Vs. V_{OL} (standard drive strength) (V_{DD} = 5 V)****Typical I_{OL} Vs. V_{OL}(low drive strength) (V_{DD} = 3 V)****Figure 6. Typical I_{OL} Vs. V_{OL} (standard drive strength) (V_{DD} = 3 V)**

5.1.2 Supply current characteristics

This section includes information about power supply current in various operating modes.

Table 4. Supply current characteristics

Num	C	Parameter	Symbol	Bus Freq	V _{DD} (V)	Typical ¹	Max	Unit	Temp
1	C	Run supply current FEI mode, all modules on; run from flash	R _{I_{DD}}	20 MHz	5	12.6	—	mA	-40 to 125 °C
	C			10 MHz		7.2	—		
	C			1 MHz		2.4	—		
	C			20 MHz	3	9.6	—		
	C			10 MHz		6.1	—		
	C			1 MHz		2.1	—		
2	C	Run supply current FEI mode, all modules off & gated; run from flash	R _{I_{DD}}	20 MHz	5	10.5	—	mA	-40 to 125 °C
	C			10 MHz		6.2	—		
	C			1 MHz		2.3	—		
	C			20 MHz	3	7.4	—		
	C			10 MHz		5.0	—		
	C			1 MHz		2.0	—		
3	P	Run supply current FBE mode, all modules on; run from RAM	R _{I_{DD}}	20 MHz	5	12.1	14.8	mA	-40 to 125 °C
	C			10 MHz		6.5	—		
	C			1 MHz		1.8	—		
	P			20 MHz	3	9.1	11.8		
	C			10 MHz		5.5	—		
	C			1 MHz		1.5	—		
4	P	Run supply current FBE mode, all modules off & gated; run from RAM	R _{I_{DD}}	20 MHz	5	9.8	12.3	mA	-40 to 125 °C
	C			10 MHz		5.4	—		
	C			1 MHz		1.6	—		
	P			20 MHz	3	6.9	9.2		
	C			10 MHz		4.4	—		
	C			1 MHz		1.4	—		
5	C	Wait mode current FEI mode, all modules on	W _{I_{DD}}	20 MHz	5	7.8	—	mA	-40 to 125 °C
	C			10 MHz		4.5	—		
	C			1 MHz		1.3	—		
	C			20 MHz	3	5.1	—		
	C			10 MHz		3.5	—		
	C			1 MHz		1.2	—		
6	C	Stop3 mode supply current no clocks active (except 1 kHz LPO clock) ^{2, 3}	S3I _{DD}	—	5	3.8	—	µA	-40 to 125 °C
	C			—	3	3	—		-40 to 125 °C

Table continues on the next page...

Table 4. Supply current characteristics (continued)

Num	C	Parameter	Symbol	Bus Freq	V _{DD} (V)	Typical ¹	Max	Unit	Temp
7	C	ADC adder to stop3 ADLPC = 1 ADLSMP = 1 ADCO = 1 MODE = 10B ADICLK = 11B	—	—	5	44	—	μA	-40 to 125 °C
	C				3	40	—		
8	C	TSI adder to stop3 ⁴ PS = 010B NSCN = 0x0F EXTCHRG = 0 REFCHRG = 0 DVOLT = 01B	—	—	5	111	—	μA	-40 to 125 °C
	C				3	110	—		
9	C	LVD adder to stop3 ⁵	—	—	5	130	—	μA	-40 to 125 °C
	C				3	125	—		

1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
2. RTC adder cause <1 μA I_{DD} increase typically, RTC clock source is 1 kHz LPO clock.
3. ACMP adder cause <1 μA I_{DD} increase typically.
4. The current varies with TSI configuration and capacity of touch electrode. Please refer to [TSI electrical specifications](#).
5. LVD is periodically woken up from stop3 by 5% duty cycle. The period is equal to or less than 2 ms.

5.1.3 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

5.1.3.1 EMC radiated emissions operating behaviors

5.2.2 Debug trace timing specifications

Table 6. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
t_{cyc}	Clock period		Frequency dependent	MHz
t_{wl}	Low pulse width	2	—	ns
t_{wh}	High pulse width	2	—	ns
t_r	Clock and data rise time	—	3	ns
t_f	Clock and data fall time	—	3	ns
t_s	Data setup	3	—	ns
t_h	Data hold	2	—	ns

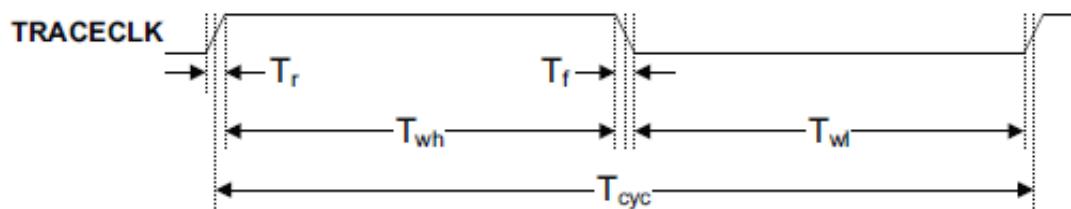


Figure 11. TRACE_CLKOUT specifications

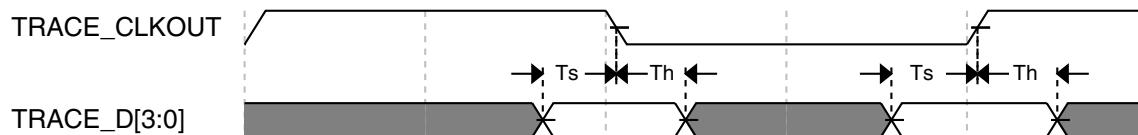


Figure 12. Trace data specifications

5.2.3 FTM module timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

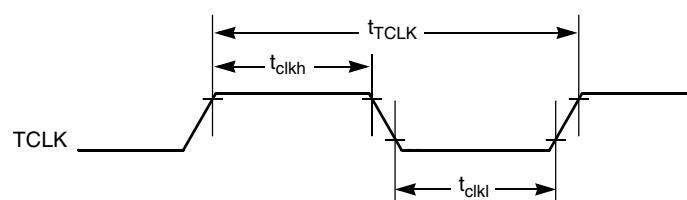
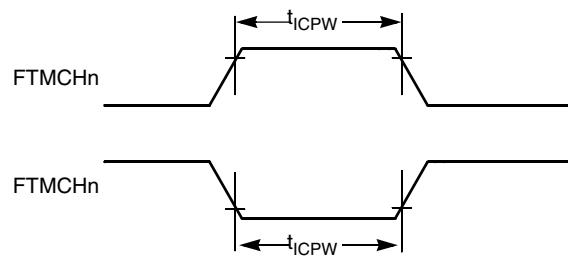
Table 7. FTM input timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz

Table continues on the next page...

Table 7. FTM input timing (continued)

No.	C	Function	Symbol	Min	Max	Unit
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkL}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

**Figure 13. Timer external clock****Figure 14. Timer input capture pulse**

5.3 Thermal specifications

5.3.1 Thermal characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 8. Thermal characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T _A	T _L to T _H -40 to 125	°C
Junction temperature range	T _J	-40 to 135	°C
Thermal resistance single-layer board			
64-pin LQFP	θ _{JA}	71	°C/W
48-pin LQFP	θ _{JA}	81	°C/W
32-pin LQFP	θ _{JA}	86	°C/W
Thermal resistance four-layer board			
64-pin LQFP	θ _{JA}	53	°C/W
48-pin LQFP	θ _{JA}	57	°C/W
32-pin LQFP	θ _{JA}	57	°C/W

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA})$$

Where:

T_A = Ambient temperature, °C

θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W

$$P_D = P_{int} + P_{I/O}$$

P_{int} = I_{DD} × V_{DD}, Watts - chip internal power

P_{I/O} = Power dissipation on input and output pins - user determined

For most applications, P_{I/O} << P_{int} and can be neglected. An approximate relationship between P_D and T_J (if P_{I/O} is neglected) is:

$$P_D = K \div (T_J + 273 \text{ °C})$$

Solving the equations above for K gives:

$$K = P_D \times (T_A + 273 \text{ °C}) + \theta_{JA} \times (P_D)^2$$

where K is a constant pertaining to the particular part. K can be determined by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving the above equations iteratively for any value of T_A.

6 Peripheral operating requirements and behaviors

6.2 NVM specifications

This section provides details about program/erase times and program/erase endurance for the flash and EEPROM memories.

Table 10. Flash characteristics

C	Characteristic	Symbol	Min ¹	Typical ²	Max ³	Unit ⁴
D	Supply voltage for program/erase -40 °C to 125 °C	V _{prog/erase}	2.7	—	5.5	V
D	Supply voltage for read operation	V _{Read}	2.7	—	5.5	V
D	NVM Bus frequency	f _{NVMBUS}	1	—	25	MHz
D	NVM Operating frequency	f _{NVMOP}	0.8	1	1.05	MHz
D	Erase Verify All Blocks	t _{VFYALL}	—	—	17338	t _{cyc}
D	Erase Verify Flash Block	t _{RD1BLK}	—	—	16913	t _{cyc}
D	Erase Verify EEPROM Block	t _{RD1BLK}	—	—	810	t _{cyc}
D	Erase Verify Flash Section	t _{RD1SEC}	—	—	484	t _{cyc}
D	Erase Verify EEPROM Section	t _{DRD1SEC}	—	—	555	t _{cyc}
D	Read Once	t _{RDONCE}	—	—	450	t _{cyc}
D	Program Flash (2 word)	t _{PGM2}	0.12	0.12	0.29	ms
D	Program Flash (4 word)	t _{PGM4}	0.20	0.21	0.46	ms
D	Program Once	t _{PGMONCE}	0.20	0.21	0.21	ms
D	Program EEPROM (1 Byte)	t _{DPGM1}	0.10	0.10	0.27	ms
D	Program EEPROM (2 Byte)	t _{DPGM2}	0.17	0.18	0.43	ms
D	Program EEPROM (3 Byte)	t _{DPGM3}	0.25	0.26	0.60	ms
D	Program EEPROM (4 Byte)	t _{DPGM4}	0.32	0.33	0.77	ms
D	Erase All Blocks	t _{ERSALL}	96.01	100.78	101.49	ms
D	Erase Flash Block	t _{ERSBLK}	95.98	100.75	101.44	ms
D	Erase Flash Sector	t _{ERSPG}	19.10	20.05	20.08	ms
D	Erase EEPROM Sector	t _{DERSPG}	4.81	5.05	20.57	ms
D	Unsecure Flash	t _{UNSECU}	96.01	100.78	101.48	ms
D	Verify Backdoor Access Key	t _{VFYKEY}	—	—	464	t _{cyc}
D	Set User Margin Level	t _{MLOADU}	—	—	407	t _{cyc}
C	FLASH Program/erase endurance T _L to T _H = -40 °C to 125 °C	n _{FLPE}	10 k	100 k	—	Cycles
C	EEPROM Program/erase endurance TL to TH = -40 °C to 125 °C	n _{FLPE}	50 k	500 k	—	Cycles
C	Data retention at an average junction temperature of T _{Javg} = 85°C after up to 10,000 program/erase cycles	t _{D_ret}	15	100	—	years

1. Minimum times are based on maximum f_{NVMOP} and maximum f_{NVMBUS}

2. Typical times are based on typical f_{NVMOP} and maximum f_{NVMBUS}

3. Maximum times are based on typical f_{NVMOP} and typical f_{NVMBUS} plus aging

4. t_{cyc} = 1 / f_{NVMBUS}

6.3.2 Analog comparator (ACMP) electricals

Table 13. Comparator electrical specifications

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DDA}	2.7	—	5.5	V
T	Supply current (Operation mode)	I_{DDA}	—	10	20	μA
D	Analog input voltage	V_{AIN}	$V_{SS} - 0.3$	—	V_{DDA}	V
P	Analog input offset voltage	V_{AIO}	—	—	40	mV
C	Analog comparator hysteresis ($HYST=0$)	V_H	—	15	20	mV
C	Analog comparator hysteresis ($HYST=1$)	V_H	—	20	30	mV
T	Supply current (Off mode)	I_{DDAOFF}	—	60	—	nA
C	Propagation Delay	t_D	—	0.4	1	μs

6.4 Communication interfaces

6.4.1 SPI switching specifications

The serial peripheral interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the chip's reference manual for information about the modified transfer formats used for communicating with slower peripheral devices. All timing is shown with respect to 20% V_{DD} and 70% V_{DD} , unless noted, and 100 pF load on all SPI pins. All timing assumes slew rate control is disabled and high drive strength is enabled for SPI output pins.

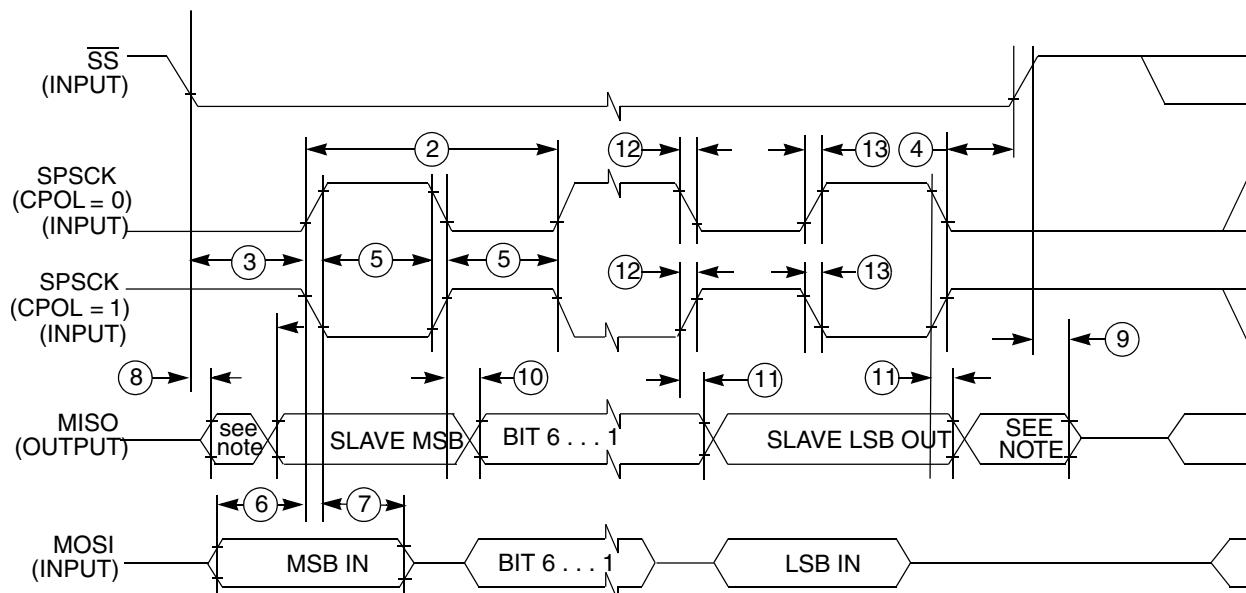
Table 14. SPI master mode timing

Nu. m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	$f_{Bus}/2048$	$f_{Bus}/2$	Hz	f_{Bus} is the bus clock
2	t_{SPSCK}	SPSCK period	$2 \times t_{Bus}$	$2048 \times t_{Bus}$	ns	$t_{Bus} = 1/f_{Bus}$
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	$t_{Bus} - 30$	$1024 \times t_{Bus}$	ns	—
6	t_{SU}	Data setup time (inputs)	15	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	25	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—

Table continues on the next page...

Table 15. SPI slave mode timing

Nu. m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	0	$f_{Bus}/4$	Hz	f_{Bus} is the bus clock as defined in .
2	t_{SPSCK}	SPSCK period	$4 \times t_{Bus}$	—	ns	$t_{Bus} = 1/f_{Bus}$
3	t_{Lead}	Enable lead time	1	—	t_{Bus}	—
4	t_{Lag}	Enable lag time	1	—	t_{Bus}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	$t_{Bus} - 30$	—	ns	—
6	t_{SU}	Data setup time (inputs)	15	—	ns	—
7	t_{HI}	Data hold time (inputs)	25	—	ns	—
8	t_a	Slave access time	—	t_{Bus}	ns	Time to data active from high-impedance state
9	t_{dis}	Slave MISO disable time	—	t_{Bus}	ns	Hold time to high-impedance state
10	t_v	Data valid (after SPSCK edge)	—	25	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{Bus} - 25$	ns	—
	t_{FI}	Fall time input	—	—	—	—
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output	—	—	—	—

**Figure 19. SPI slave mode timing (CPHA = 0)**

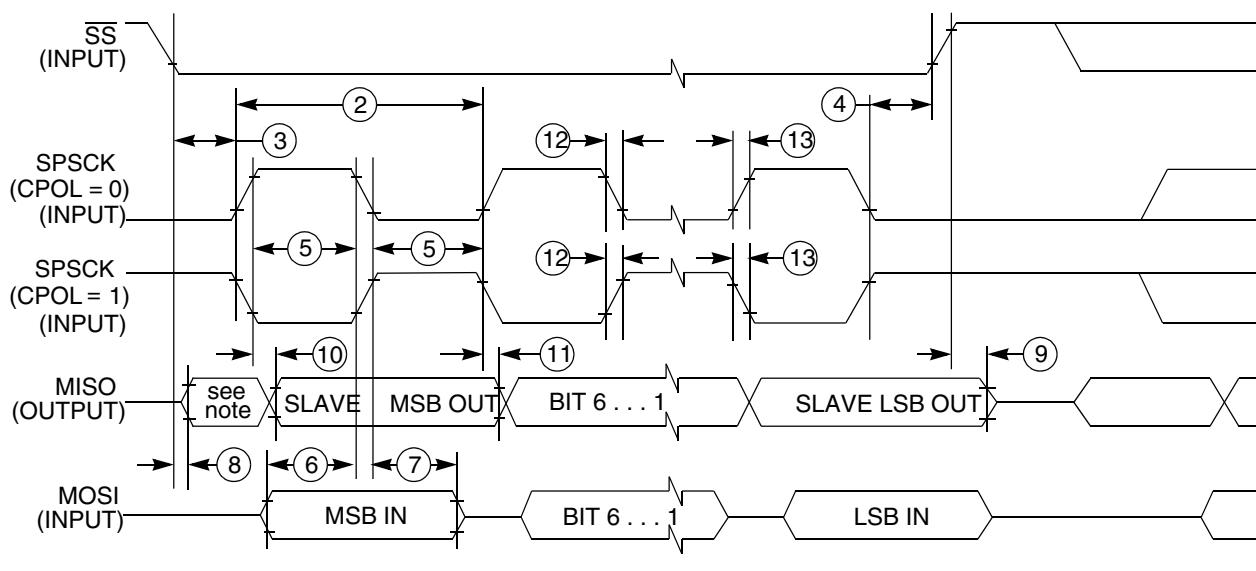


Figure 20. SPI slave mode timing (CPHA=1)

6.5 Human-machine interfaces (HMI)

6.5.1 TSI electrical specifications

Table 16. TSI electrical specifications

Symbol	Description	Min.	Type	Max	Unit
TSI_RUNF	Fixed power consumption in run mode	—	100	—	µA
TSI_RUNV	Variable power consumption in run mode (depends on oscillator's current selection)	1.0	—	128	µA
TSI_EN	Power consumption in enable mode	—	100	—	µA
TSI_DIS	Power consumption in disable mode	—	1.2	—	µA
TSI_TEN	TSI analog enable time	—	66	—	µs
TSI_CREF	TSI reference capacitor	—	1.0	—	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	-10	—	10	%

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin LQFP	98ASH70029A
48-pin LQFP	98ASH00962A
64-pin LQFP	98ASS23234W

8 Pinout

8.1 Signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

Table 17. Pin availability by package pin-count

Pin Number			Lowest Priority <--> Highest				
64-LQFP	48-LQFP	32-LQFP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
1	1	1	PTD1 ^{1, 1}	KBI1P1	FTM2CH3	MOSI1	—
2	2	2	PTD0 ¹	KBI1P0	FTM2CH2	SPSCK1	—
3	—	—	PTH7	—	—	—	—
4	—	—	PTH6	—	—	—	—
5	3	—	PTE7	—	TCLK2	—	—
6	4	—	PTH2	—	BUSOUT	—	—
7	5	3	—	—	—	—	V _{DD}
8	6	4	—	—	—	V _{DDA}	V _{REFH}
9	7	5	—	—	—	V _{SSA}	V _{REFL}
10	8	6	—	—	—	—	V _{SS}
11	9	7	PTB7	—	SCL	—	EXTAL
12	10	8	PTB6	—	SDA	—	XTAL
13	11	—	—	—	—	—	V _{SS}
14	—	—	PTH1 ¹	—	FTM2CH1	—	—
15	—	—	PTH0 ¹	—	FTM2CH0	—	—
16	12	—	PTE6	—	—	—	—
17	13	—	PTE5	—	—	—	—
18	14	9	PTB5 ¹	FTM2CH5	SS0	—	—
19	15	10	PTB4 ¹	FTM2CH4	MISO0	—	—

Table continues on the next page...

Table 17. Pin availability by package pin-count (continued)

Pin Number			Lowest Priority <-- --> Highest				
64-LQFP	48-LQFP	32-LQFP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
58	—	—	PTG0	—	—	—	—
59	43	—	PTE1 ¹	—	MOSI0	—	—
60	44	—	PTE0 ¹	—	SPSCK0	TCLK1	—
61	45	29	PTC5	—	FTM1CH1	—	—
62	46	30	PTC4	—	FTM1CH0	RTCO	—
63	47	31	—	—	—	—	RESET
64	48	32	—	—	—	BKGD	MS

1. This is a high current drive pin when operated as output.
2. This is a true open-drain pin when operated as output.

Note

When an alternative function is first enabled, it is possible to get a spurious edge to the module. User software must clear any associated flags before interrupts are enabled. The table above illustrates the priority if multiple modules are enabled. The highest priority module will have control over the pin. Selecting a higher priority pin function with a lower priority function already enabled can cause spurious edges to the lower priority module. Disable all modules that share a pin before enabling another module.

8.2 Device pin assignment

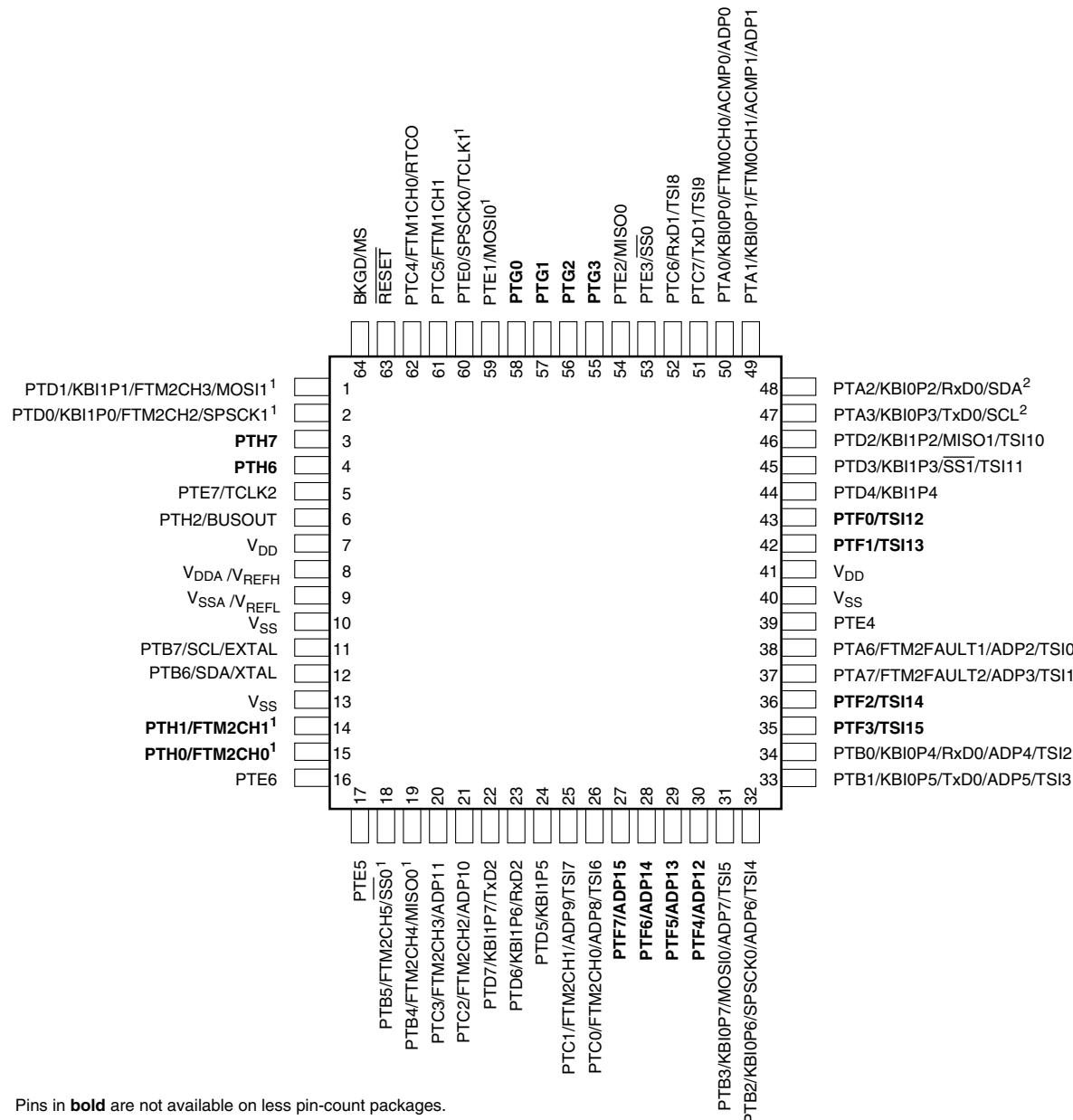


Figure 21. S9S08RN60 64-pin LQFP package

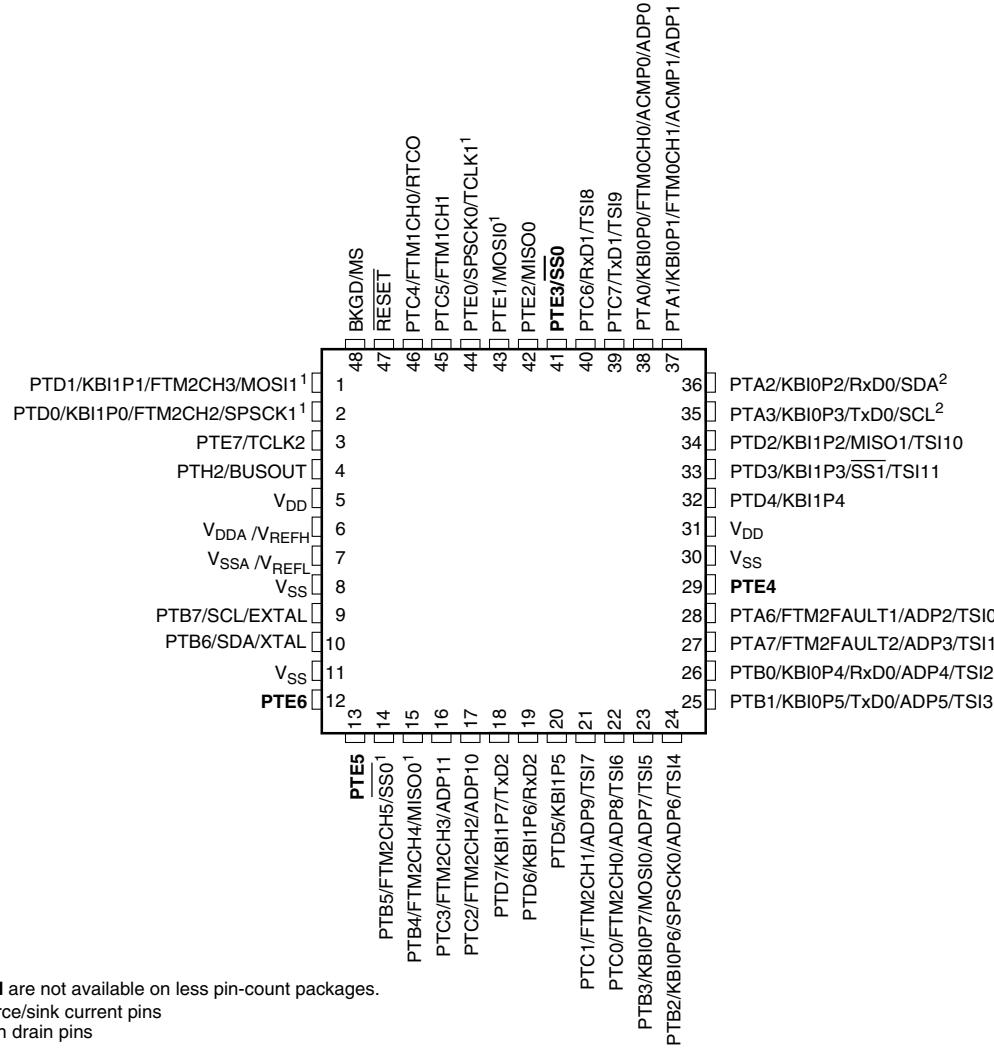
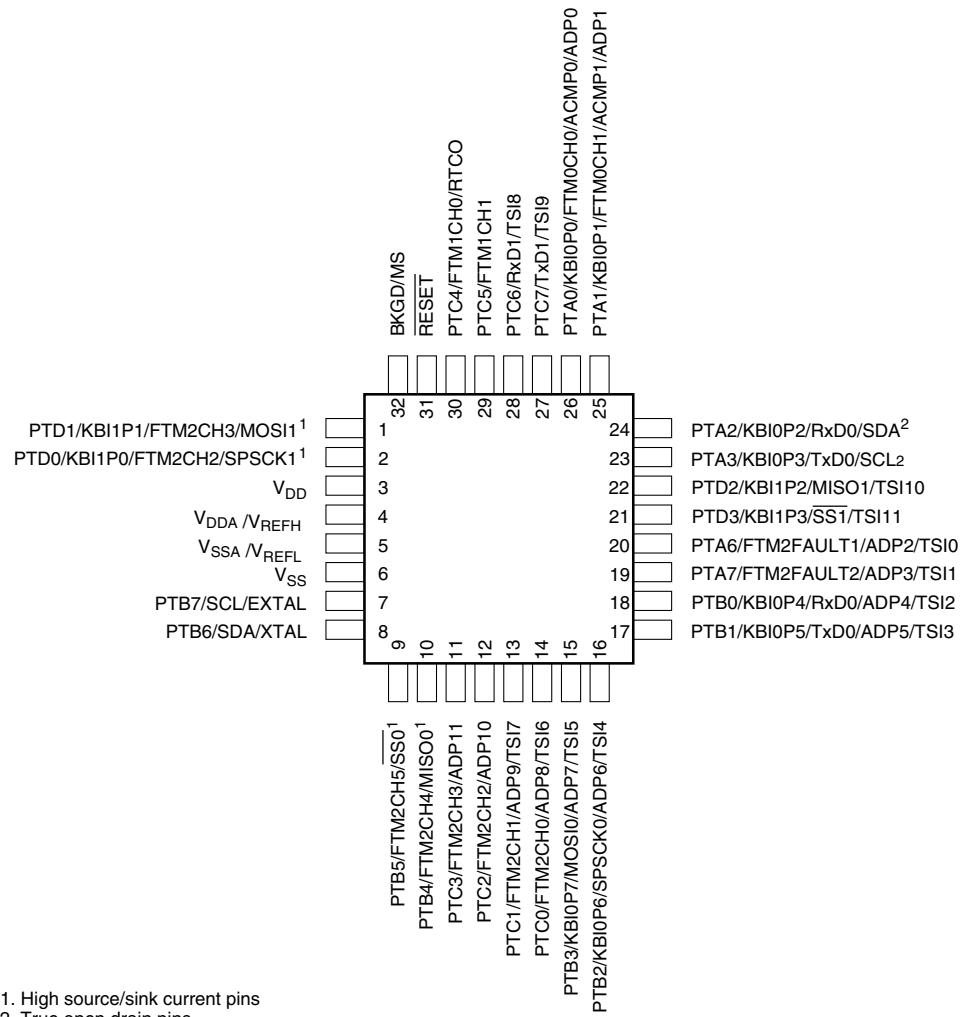


Figure 22. S9S08RN60 48-pin LQFP package

**Figure 23. S9S08RN60 32-pin LQFP package**

9 Revision history

The following table provides a revision history for this document.

Table 18. Revision history

Rev. No.	Date	Substantial Changes
1	01/2014	Initial Release